

High Voltage Transistor

PNP Silicon

MMBT5401L, SMMBT5401L, NSVMMBT5401L

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

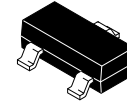
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	-150	Vdc
Collector – Base Voltage	V_{CBO}	-160	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

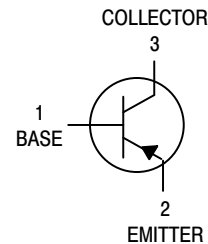
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

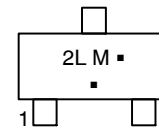
- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



- 2L = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
NSVMMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = -1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-150	–	Vdc
Collector–Base Breakdown Voltage ($I_C = -100\text{ }\mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	-160	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	–	Vdc
Collector–Base Cutoff Current ($V_{CB} = -120\text{ Vdc}$, $I_E = 0$) ($V_{CB} = -120\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	I_{CBO}	– –	-50 -50	nAdc μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = -1.0\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$) ($I_C = -10\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$) ($I_C = -50\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$)	h_{FE}	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -1.0\text{ mA}$) ($I_C = -50\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{CE(sat)}$	– –	-0.2 -0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -1.0\text{ mA}$) ($I_C = -50\text{ mA}$, $I_B = -5.0\text{ mA}$)	$V_{BE(sat)}$	– –	-1.0 -1.0	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	300	MHz
Output Capacitance ($V_{CB} = -10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	6.0	pF
Small Signal Current Gain ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	40	200	–
Noise Figure ($I_C = -200\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 10\text{ }\Omega$, $f = 1.0\text{ kHz}$)	NF	–	8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



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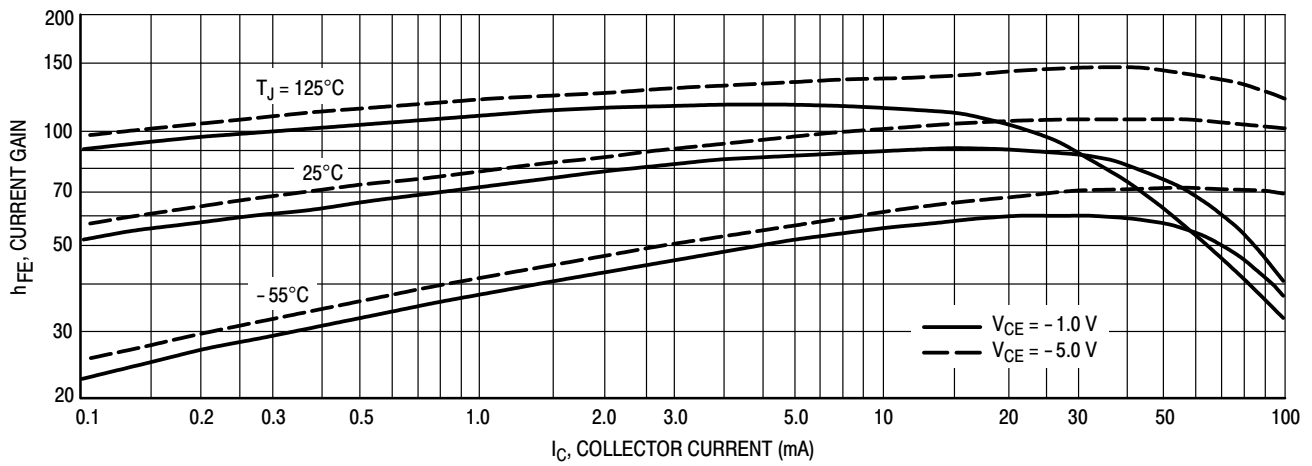


Figure 1. DC Current Gain

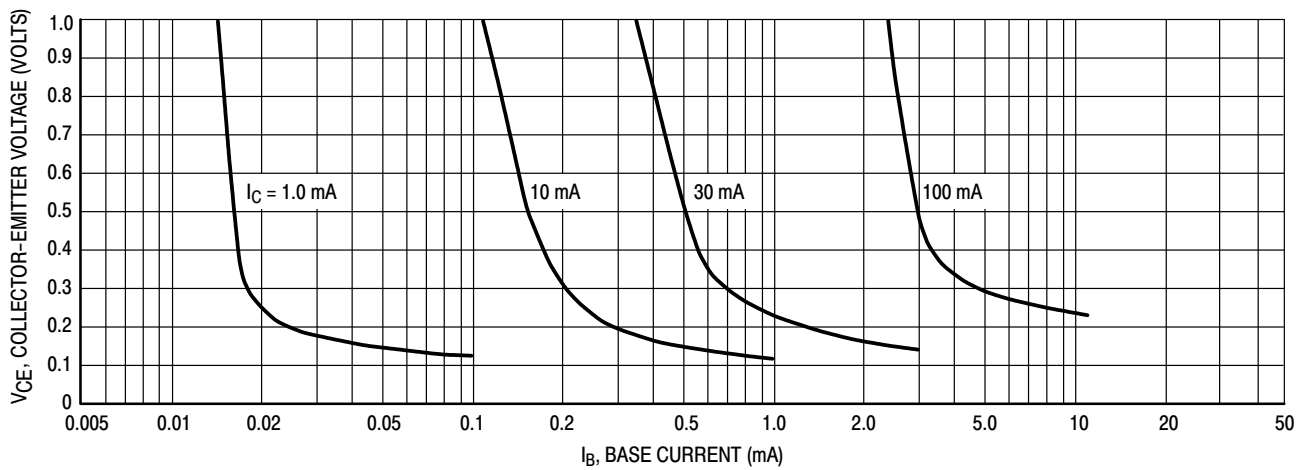


Figure 2. Collector Saturation Region

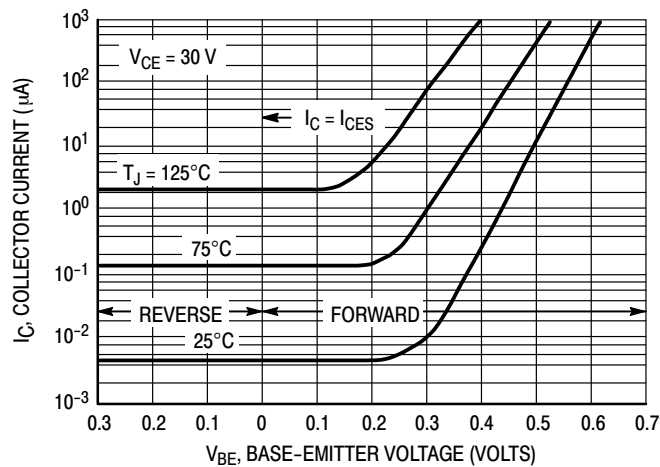


Figure 3. Collector Cut-Off Region

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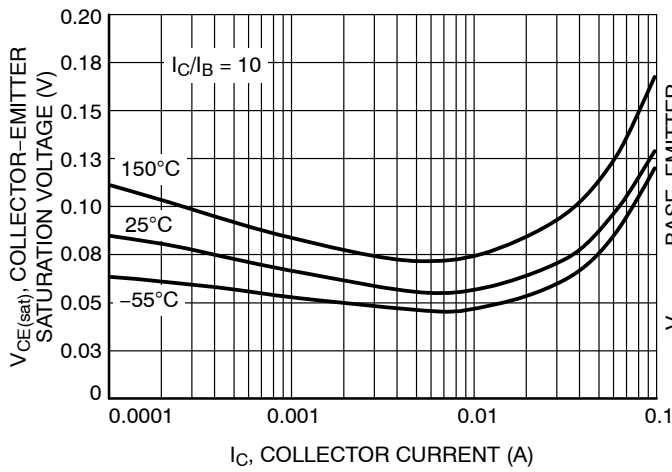


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

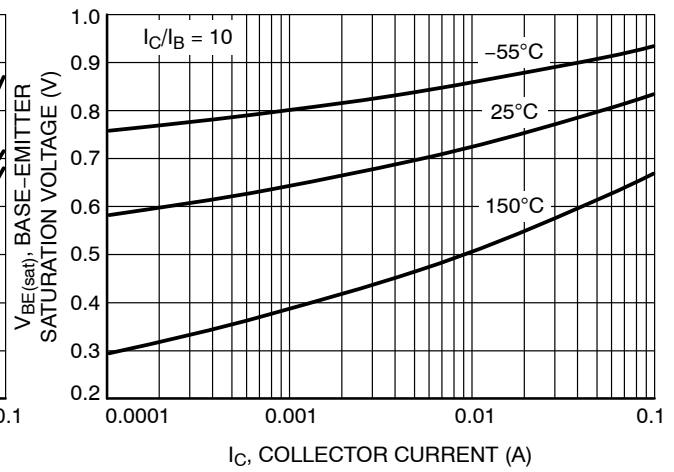


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

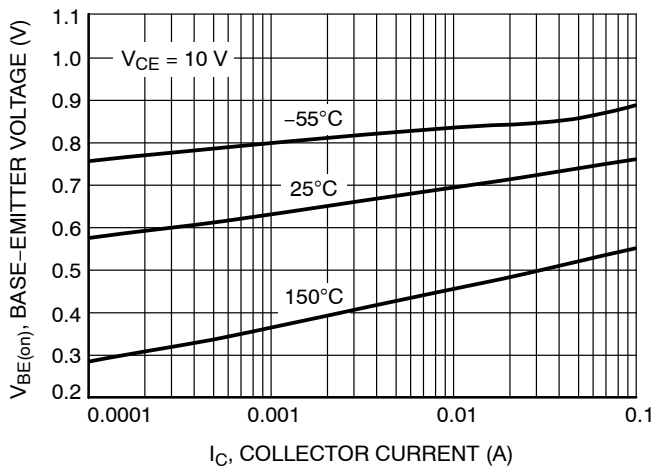


Figure 6. Base-Emitter Voltage vs. Collector Current

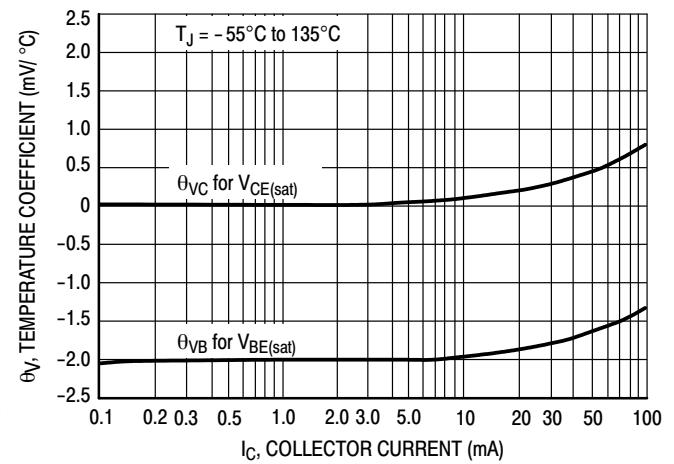
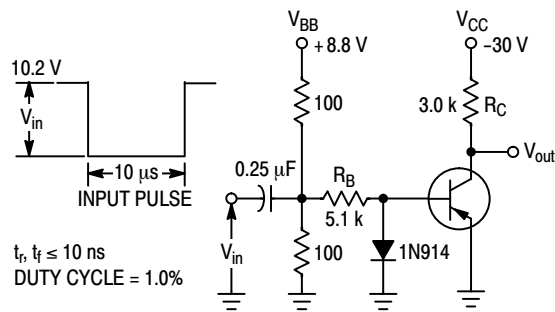


Figure 7. Temperature Coefficients



Values Shown are for I_C @ 10 mA

Figure 8. Switching Time Test Circuit

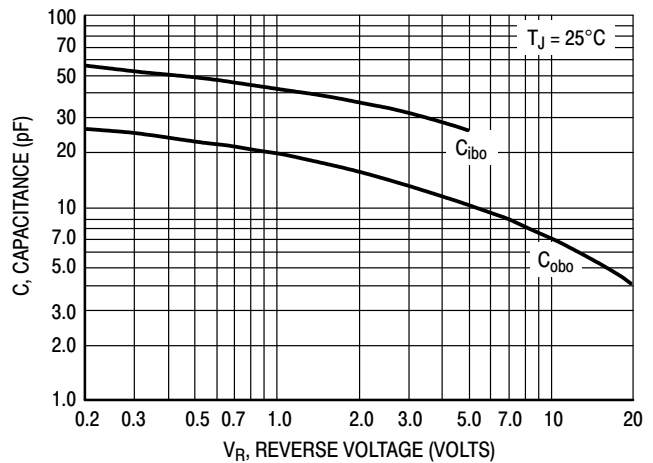


Figure 9. Capacitances

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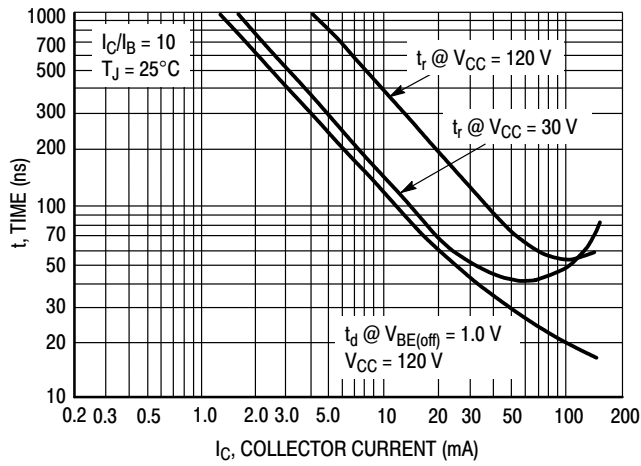


Figure 10. Turn-On Time

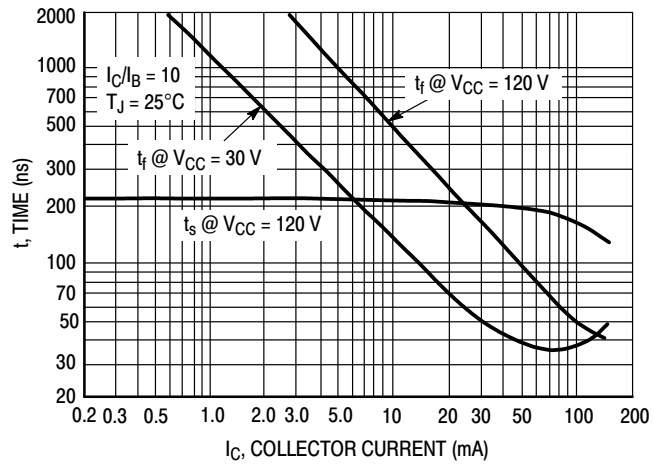


Figure 11. Turn-Off Time

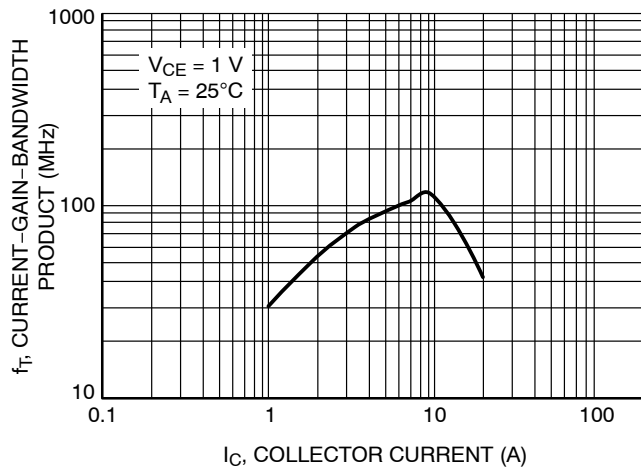


Figure 12. Current Gain Bandwidth Product

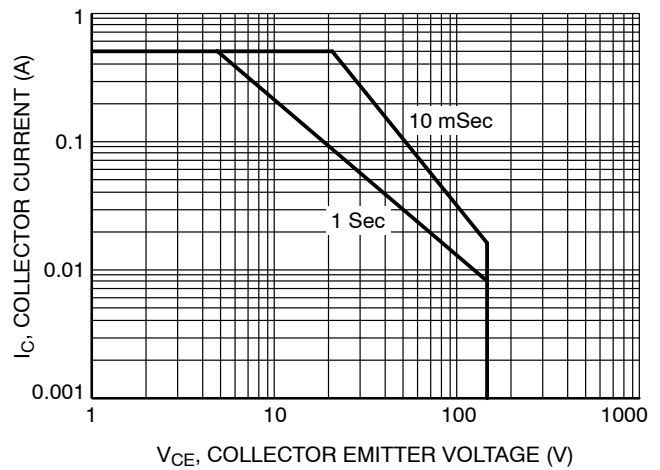


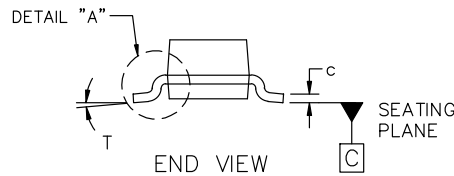
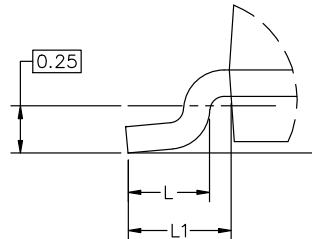
Figure 13. Safe Operating Area



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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